II. Amendments (including status) of Claims

Claims 1-12 (withdrawn).

13. (Currently Amended) A semiconductor device comprising:

a semiconductor substrate; and

a semiconductor element which comprises:

a first electrode provided on a front plane of said semiconductor substrate, and a second electrode provided on a rear plane of said semiconductor substrate[:];

a first metallic member connected to said first electrode; and

a second metallic member connected to said second electrode; wherein

said second electrode is connected to said second metallic member via a metallic layer containing precious metal, and

said metallic layer is [composed by bonding to each other] a composite metal layer comprised of a first precious metal layer provided at the [bonding] front plane of said second electrode [with] and a second precious metal layer adhered thereto by compression bonding provided at the [bonding] front plane of said second metallic member.

Claims 14-18 (withdrawn).

19. (Currently Amended) A semiconductor device comprising:

a semiconductor chip; and

a metallic member connected to a chip electrode, wherein:

said chip electrode is composed of any of an Al film and an Al alloy film;

a bonding front plane of said metallic member is composed of a plated precious metal film;

said chip electrode is bonded metallically to said metallic member via Au bumps; and

[an aluminum film of more than] at least 80% [in] of an area of [an] a respective Au/Al bonding region is [made all] contacting a Au bump, said bonding region being made of an Au/Al alloy layer in the thickness direction.

20. (Currently Amended) A semiconductor device comprising:

a semiconductor chip;

[a first metallic member connected to chip rear plane electrode;]

a [second] first metallic member connected to a main current electrode on a circuit forming front plane of the chip; and

a second metallic member connected to a chip rear plane electrode;

a third metallic member connected to a control electrode on the front plane of the chip; wherein:

said main current electrode and said control electrode are composed of any of an Al film and an Al alloy film;

plural Au bumps are formed on the Al electrode film in a metallically bonded condition;

each of said [second] first and [third] second metallic members, which are plated with a precious metal, has such a structure that [said metallic member] each is bonded with said Au bumps by compression bonding, and gaps between [said] the metallic members and said chip are filled with resin; and

a plane of said [first] second metallic member opposite to said chip in [the plane of chip projection] a plan view projected direction of the chip, and planes of said [second] first and third metallic members opposite to said chip are exposed to the surface of said semiconductor device.

Claims 21-24 (withdrawn).

25. (New) A semiconductor device comprising:

a semiconductor chip;

a first metallic member connected to a main current electrode on a circuit forming front plane of the chip; and

a second metallic member connected to a chip rear plane electrode;

a third metallic member connected to a control electrode on the front plane of the chip; wherein:

said main current electrode and said control electrode are composed of any of an Al film and an Al alloy film;

plural Au bumps are formed on the Al electrode film in a metallically bonded condition;

each of said first and second metallic members, which are plated with a precious metal, has such a structure that each is bonded with said Au bumps by compression bonding, and gaps between the metallic members and said chip are filled with resin; and

a plane of said second metallic member opposite to said chip in a plan view projected direction of the chip is exposed to the surface of said semiconductor device.